SENSITRON SEMICONDUCTOR

TECHNICAL DATA DATA SHEET 528, REV. B

SILICON SCHOTTKY RECTIFIER DIE Ultra Low Reverse Leakage 200°C Operating Temperature

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging
- Out Performs 100 Volt Ultrafast Rectifiers

Maximum Ratings:

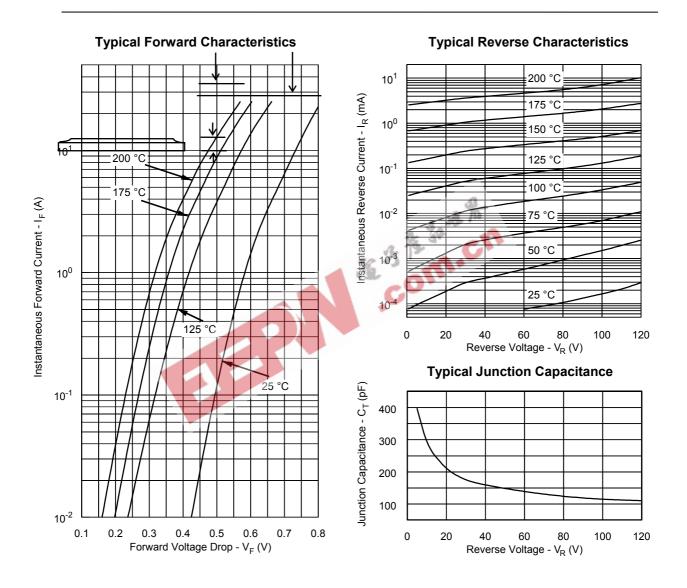
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	100	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	15	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave ⁽¹⁾	280	A
Non-Repetitive Avalanche Energy	E_{AS}	T _J = 25 °C, I _{AS} = 0.53 A, L = 56 mH	8.0	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 µs f limited by $T_J max V_A=1.5V_R$	0.53	A
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	T _{stg}	-	-65 to +200	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.84	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.68	V
Max. Reverse Current	I _{R1}	@V _R = 100V, Pulse,	10	μA
		T _J = 25 °C		
	I _{R2}	@V _R = 100V, Pulse,	1.0	mA
		T _J = 125 °C		
Max. Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C	500	pF
		f _{SIG} = 1MHz,		
		V _{SIG} = 50mV (p-p)		

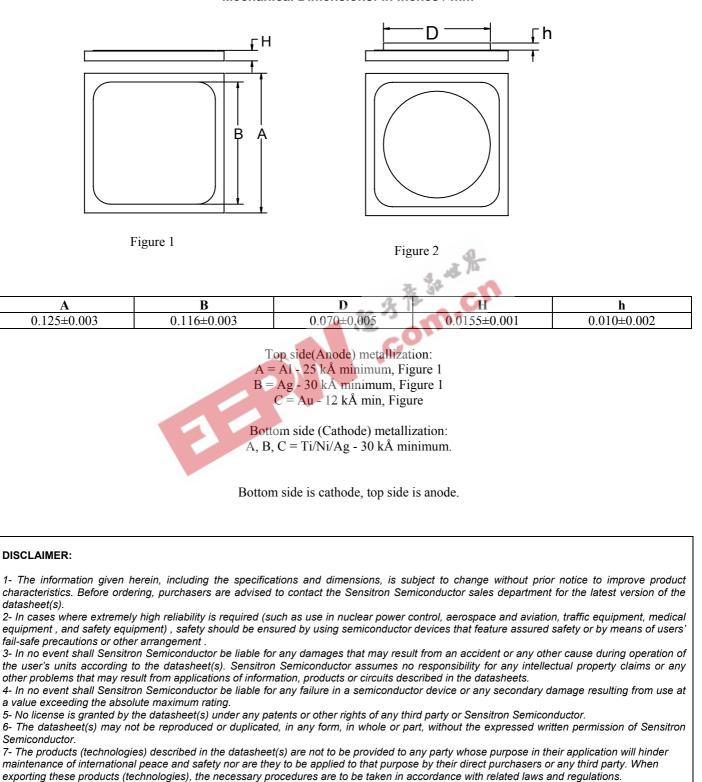
(1) in SHD package

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Mechanical Dimensions: In Inches / mm